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Claim Amendments:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A single crystal spinel wafer, comprising:  
a front face and a back face; and  
an outer periphery having first and second flats, wherein the first flat indicates an orientation of a cleavage plane of the wafer, a cleavage plane of the wafer intersects the front face at a locus of points extending along a line, the line being parallel to the first flat, and the second flat indicates a direction of cleavage propagation of the cleavage plane.
2. (Original) The single crystal spinel wafer of claim 1, wherein the wafer has a  $\langle 111 \rangle$  crystallographic orientation.
3. (Original) The single crystal spinel wafer of claim 1, wherein the front and back faces of the wafer extend along a  $\{111\}$  crystal plane.
4. (Canceled)
5. (Canceled)
6. (Currently Amended) The single crystal spinel wafer of claim ~~[[5]]~~1, wherein the first flat extends along a plane in the  $\{2\ 2\ -4\}$  and  $\{1\ 1\ -2\}$  plane families.
7. (Canceled)
8. (Currently Amended) The single crystal spinel wafer of claim ~~[[5]]~~1, wherein the second flat identifies the front and back surfaces of the wafer.

9. (Currently Amended) The single crystal spinel wafer of claim ~~[[5]]~~1, wherein the cleavage plane makes angle of about 55 degrees with respect to the front face.

10. (Currently Amended) ~~[[A]]~~The single crystal spinel wafer of claim 1, ~~comprising:~~  
~~a front face and a back face; and~~  
~~an outer periphery having first and second flats, wherein the second flat extends along a~~  
plane in the {02-2}, {01-1}, {22-4} and {11-2} plane families, which is non-  
parallel to the plane of the major flat.

11. (Canceled).

12. (Original) The single crystal spinel wafer of claim 1, wherein a normal to the first flat and a normal to the second flat lie in the same plane such that the normals intersect each other, and the normals make an angle of 60, 90, 120, or 150 degrees.

13. (Original) The single crystal spinel wafer of claim 1, wherein the wafer comprises non-stoichiometric spinel.

14. (Original) The single crystal spinel wafer of claim 13, wherein the wafer has a composition is represented by the general formula  $aAD \cdot bE_2D_3$ , wherein A is selected from the group consisting of Mg, Ca, Zn, Mn, Ba, Sr, Cd, Fe, and combinations thereof, E is selected from the group consisting Al, In, Cr, Sc, Lu, Fe, and combinations thereof, and D is selected from the group consisting O, S, Se, and combinations thereof, wherein a ratio  $b:a > 1:1$  such that the spinel is rich in  $E_2D_3$ .

15. (Original) The single crystal spinel wafer of claim 14, wherein A is Mg, D is O, and E is Al, such that the single crystal spinel has the formula  $aMgO \cdot bAl_2O_3$ .

16. (Original) The single crystal spinel wafer of claim 14, wherein the ratio  $b:a$  is not less than about 1.2:1.

17. (Original) The single crystal spinel wafer of claim 14, wherein the ratio b:a is not less than about 1.5:1.

18. (Original) The single crystal spinel wafer of claim 14, wherein the ratio b:a is not less than about 2.0:1.

19. (Original) The single crystal spinel wafer of claim 14, wherein the ratio b:a is not less than about 2.5:1.

20. (Original) The single crystal spinel wafer of claim 14, wherein the ratio b:a is not greater than about 4:1.

21. (Original) The single crystal spinel wafer of claim 14, wherein the wafer has a lower mechanical stress and strain compared to stoichiometric spinel.

22. (Original) The single crystal spinel wafer of claim 1, further comprising an active layer, the active layer comprising a nitride semiconductor layer.

23. (Original) The single crystal spinel wafer of claim 22, wherein the nitride semiconductor layer comprises  $\text{Al}_x\text{Ga}_{1-x-y}\text{In}_y\text{N}$ , where  $0 \leq x \leq 0.25$  and  $0 \leq y \leq 0.5$ .

24. (Canceled)

25. (Original) The single crystal spinel wafer of claim 1, wherein first flat is a major flat, and the second flat is a minor flat.

26. (Original) An active device provided on the wafer of claim 1.

27. (Previously Presented) The device of claim 26, wherein the device is an optoelectronic device selected from the group consisting of a laser and LED.

28. (Canceled)

29. (Canceled)

30. (Canceled)

31. (Currently Amended) The wafer of claim ~~[[28]]~~1, wherein the cleavage plane intersects the bottom face along a locus of points forming a second line, wherein the cleavage plane is oriented such that the cleavage plane slopes away from the first flat and that the second line is located a distance from the first flat that is greater than a distance between the first line and the first flat.

32. (Original) The wafer of claim 31, wherein the first flat is a major flat, the second flat is a minor flat.

33. (Original) The wafer of claim 31, wherein the second flat is positioned to indicate the direction of a slope of the cleavage plane.

Claims 34-39 (Canceled).

40. (New) A single crystal spinel wafer, comprising:  
a front face and a back face; and  
an outer periphery having first and second flats, wherein the first flat indicates an orientation of a cleavage plane of the wafer and extends along a plane in the {2 2 - 4} and {1 1 -2} plane families, the cleavage plane of the wafer intersects the front face at a locus of points extending along a line, the line being parallel to the first flat, and the second flat indicates a direction of cleavage propagation of the cleavage plane and extends along a plane in the {02-2}, {01-1}, {22-4} and {11-2} plane families.